

FEATURES

- Function, Pinout, and Drive Compatible with the FCT and F Logic
- FCT-A speed at 5.3ns max. (Com'l)
FCT speed at 6.5ns max. (Com'l)
- CMOS V_{OH} (typically = 3.3V) versions of Equivalent FCT functions
- Edge-rate Control Circuitry for Significantly Improved Noise Characteristics
- Power-off disable feature
- Matched Rise and Fall times
- Fully Compatible with TTL Input and Output Logic Levels
- 64 mA Sink Current (Com'l), 48 mA (Mil)
15 mA Source Current (Com'l), 12 mA (Mil)
- Separate Controls for Data Flow in Each Direction
- Back to Back Latches for Storage

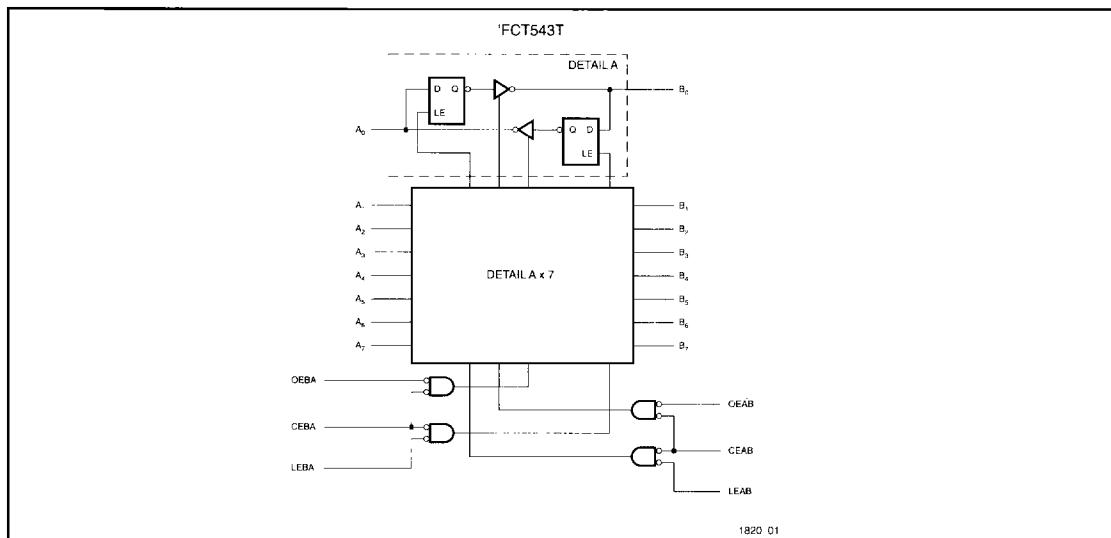
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DESCRIPTION

The 'FCT543T Octal Latched Transceiver contains two sets of eight D-type latches with separate Latch Enable (LEAB, LEBA) and Output Enable (OEAB, OEBA) controls for each set to permit independent control of inputting and outputting in either direction of data flow. For data flow from A to B, for example, the A-to-B Enable (\overline{CEAB}) input must be LOW in order to enter data from A0-A7 or to take data from B0-B7, as indicated in the truth table. With CEAB LOW, a LOW signal on the A-to-B Latch Enable

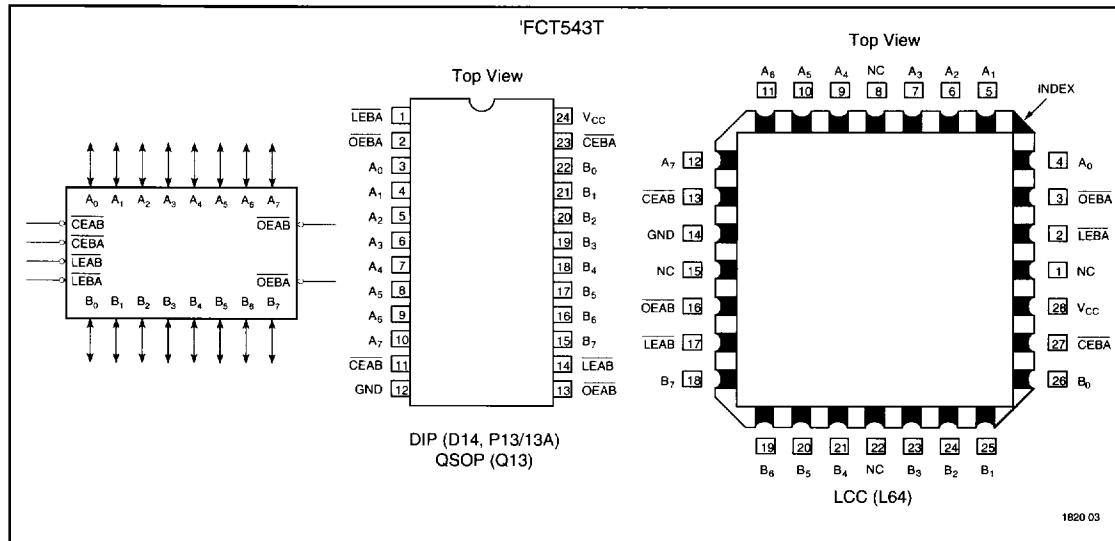
(LEAB) input makes the A-to-B latches transparent; a subsequent LOW-to-HIGH transition of the LEAB signal puts the A latches in the storage mode and their output no longer change with the A inputs. With \overline{CEAB} and \overline{OEAB} both LOW, the 3-state B output buffers are active and reflect the data present at the output of the A latches. Control of data from B to A is similar, but uses CEAB, LEAB and OEAB inputs.

FUNCTIONAL BLOCK DIAGRAM



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LOGIC SYMBOL AND PIN CONFIGURATIONS



PIN DESCRIPTIONS

Pin Name	Description
OEAB	A-to-B Output Enable Input (Active LOW)
OEBA	B-to-A Output Enable Input (Active LOW)
CEAB	A-to-B Enable Input (Active LOW)
CEBA	B-to-A Enable Input (Active LOW)
LEAB	A-to-B Latch Enable Input (Active LOW)
LEBA	B-to-A Latch Enable Input (Active LOW)
A ₀ -A ₇	A-to-B Data Inputs or B-to-A 3-State Outputs
B ₀ -B ₇	B-to-A Data Inputs or A-to-B 3-State Outputs

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ABSOLUTE MAXIMUM RATINGS^{1,2}

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	-65 to +150	°C
T _A	Ambient Temperature Under Bias	-65 to +135	°C
V _{CC}	V _{CC} Potential to Ground	-0.5 to +7.0	V
P _T	Power Dissipation	0.5	W

Notes:

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- Operation beyond the limits set forth in the above table may impair the useful life of the device. Unless otherwise noted, these limits are over the operating free-air temperature range.

Symbol	Parameter	Value	Unit
I _{OUTPUT}	Current Applied to Output	120	mA
V _{IN}	Input Voltage	-0.5 to 7.0	V
V _{OUT}	Voltage Applied to Output	-0.5 to 7.0	V

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- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.

RECOMMENDED OPERATING CONDITIONS

Free Air Ambient Temperature	Min	Max
Military	-55°C	+125°C
Commercial	0°C	+70°C

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Supply Voltage (V _{CC})	Min	Max
Military	+4.5V	+5.5V
Commercial	+4.75V	+5.25V

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DC ELECTRICAL CHARACTERISTICS (Over recommended operating conditions)

Symbol	Parameter		Min	Typ ¹	Max	Units	V _{CC}	Conditions
V _{IH}	Input HIGH Voltage		2.0			V		
V _{IL}	Input LOW Voltage			0.8		V		
V _H	Hysteresis ¹			0.2		V		All inputs
V _{IK}	Input Clamp Diode Voltage			-0.7	-1.2	V	MIN	I _{IN} = -18mA
V _{OH}	Output HIGH Voltage	Military	2.4	3.3		V	MIN	I _{OH} = -12mA
		Commercial	2.4	3.3		V	MIN	I _{OH} = -15mA
V _{OL}	Output LOW Voltage	Military		0.3	0.55	V	MIN	I _{OL} = 48mA
		Commercial		0.3	0.55	V	MIN	I _{OL} = 64mA
I _{IH}	Input HIGH Current				20	μA	MAX	V _{IN} = V _{CC}
I _{IH}	Input HIGH Current ³	Except I/O Pln			5	μA	MAX	V _{IN} = 2.7V
		I/O Pln			15	μA	MAX	V _{IN} = 2.7V
I _{IL}	Input LOW Current ³	Except I/O Pln			-5	μA	MAX	V _{IN} = 0.5V
		I/O Pins only			-15	μA	MAX	V _{IN} = 0.5V
I _{OZH}	Off State I _{OUT} HIGH-Level Output Current				15	μA	MAX	V _{OUT} = 2.7V
I _{OZL}	Off State I _{OUT} LOW-Level Output Current				-15	μA	MAX	V _{OUT} = 0.5V
I _{OS}	Output Short Circuit Current ²		-60	-120	-225	mA	MAX	V _{OUT} = 0.0V
I _{OFF}	Power-off Disable				100	μA	MAX	V _{OUT} = 4.5V
C _{IN}	Input Capacitance ³			5	10	pF		All inputs
C _{I/O}	Output Capacitance ³			9	12	pF		All outputs
I _{CC}	Quiescent Power Supply Current			0.2	1.5	mA	MAX	V _{IN} ≤ 0.2V V _{IN} ≥ V _{CC} - 0.2V

Notes:

- Typical values are at V_{CC} = 5.0V, T_A = +25°C ambient.
- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect

operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

- This parameter is guaranteed but not tested.

DC CHARACTERISTICS (Over recommended operating conditions unless otherwise specified.)

Symbol	Parameter	Typ. ¹	Max.	Units	Conditions
ΔI_{cc}	Quiescent Power Supply Current (TTL inputs)	0.5	2.0	mA	$V_{cc} = \text{MAX}$, $V_{in} = 3.4V^2$, $f_i = 0$, Outputs Open
I_{CCD}	Dynamic Power Supply Current ³	0.15	0.25	mA/MHz	$V_{cc} = \text{MAX}$, One Input Toggling, 50% Duty Cycle, $\overline{CEAB} + \overline{OEAB} = \text{Low}$, Outputs Open, $\overline{CEAB} = \text{High}$, $V_{in} \leq 0.2V$ or $V_{in} \geq V_{cc} - 0.2V$
		1.7	4.0	mA	$V_{cc} = \text{MAX}$, $f_o = 10\text{MHz}$, $\overline{CEAB} + \overline{OEAB} = \text{Low}$ 50% Duty Cycle, Outputs Open, $\overline{CEBA} = \text{High}$ One Bit Toggling at $f_i = 5\text{MHz}$, $f_o = \overline{LEAB} = 10\text{MHz}$, $V_{in} \leq 0.2V$ or $V_{in} \geq V_{cc} - 0.2V$
I_c	Total Power Supply Current ⁵	2.2	6.0	mA	$V_{cc} = \text{MAX}$, $f_o = 10\text{MHz}$, $\overline{CEAB} + \overline{OEAB} = \text{Low}$ 50% Duty Cycle, Outputs Open, $\overline{CEBA} = \text{High}$ One Bit Toggling at $f_i = 5\text{MHz}$, $f_o = \overline{LEAB} = 10\text{MHz}$, $V_{in} = 3.4V$ or $V_{in} = \text{GND}$
		7.0	12.8 ⁴	mA	$V_{cc} = \text{MAX}$, $f_o = 10\text{MHz}$, $\overline{CEAB} + \overline{OEAB} = \text{Low}$ 50% Duty Cycle, Outputs Open, $\overline{CEBA} = \text{High}$ Eight Bits Toggling at $f_i = 5\text{MHz}$, $f_o = \overline{LEAB} = 10\text{MHz}$, $V_{in} \leq 0.2V$ or $V_{in} \geq V_{cc} - 0.2V$
		9.2	21.8 ⁴	mA	$V_{cc} = \text{MAX}$, $f_o = 10\text{MHz}$, $\overline{CEAB} + \overline{OEAB} = \text{Low}$ 50% Duty Cycle, Outputs Open, $\overline{CEBA} = \text{High}$ Eight Bits Toggling at $f_i = 5\text{MHz}$, $f_o = \overline{LEAB} = 10\text{MHz}$, $V_{in} = 3.4V$ or $V_{in} = \text{GND}$

Notes:

- Typical values are at $V_{cc} = 5.0V$, $+25^\circ\text{C}$ ambient.
- Per TTL driven input ($V_{in} = 3.4V$); all other inputs at V_{cc} or GND.
- This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
- Values for these conditions are examples of the I_{cc} formula. These limits are guaranteed but not tested.
- $I_c = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
 $I_c = I_{cc} + \Delta I_{cc} D_H N_T + I_{CCD}(f_o/2 + f_i N_i)$
 I_{cc} = Quiescent Current with CMOS input levels

ΔI_{cc} = Power Supply Current for a TTL High Input ($V_{in} = 3.4V$)
 D_H = Duty Cycle for TTL Inputs High
 N_T = Number of TTL Inputs at D_H
 I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)
 f_o = Clock Frequency for Register Devices (Zero for Non-Register Devices)
 f_i = Input Frequency
 N_i = Number of Inputs at f_i
 All currents are in millamps and all frequencies are in megahertz.

TRUTH TABLE FOR A-TO-B (Symmetric with B-to-A)

Inputs			Latch Status	Outputs 'FCT543T
CEAB	LEAB	OEAB	A-TO-B	B0-B7
H	-	-	Storing	High Z
-	H	-	Storing	-
-	-	H	-	High Z
L	L	L	Transparent	Current A Inputs
L	H	L	Storing	Previous A Inputs

* = Before \overline{LEAB} LOW-to-HIGH Transition
 H = HIGH Voltage Level
 L = LOW Voltage Level
 - = Don't Care or Irrelevant
 A-to-B data flow shown: B-to-A flow control is the same, except using \overline{CEBA} , \overline{LEBA} , and \overline{OEBA}

AC CHARACTERISTICS

Sym.	Parameter	'FCT543T				'FCT543AT				'FCT543CT				Units	Fig. No.*		
		MIL		COM'L		MIL		COM'L		MIL		COM'L					
		Min. ¹	Max.														
t_{PLH} t_{PHL}	Propagation Delay Transparent Mode A_n to B_n or B_n to A_n	2.0	10.0	2.5	8.5	2.5	7.5	2.5	6.5	2.5	6.1	2.5	5.3	ns	1, 5		
t_{PLH} t_{PHL}	Propagation Delay LEBA to A_n LEAB to B_n	2.5	14.0	2.5	12.5	2.5	9.0	2.5	8.0	2.5	8.0	2.5	7.0	ns	1, 5		
t_{PZH} t_{PZL}	Output Enable Time \overline{OEBA} or \overline{OEAB} to A_n or B_n \overline{CEBA} or \overline{CEAB} to A_n or B_n	2.0	14.0	2.0	12.0	2.0	10.0	2.0	9.0	2.0	9.0	2.0	8.0	ns	1, 7, 8		
t_{PHZ} t_{PZL}	Output Disable Time \overline{OEBA} or \overline{OEAB} to A_n or B_n \overline{CEBA} or \overline{CEAB} to A_n or B_n	2.0	13.0	2.0	9.0	2.0	8.5	2.0	7.5	2.0	7.5	2.0	6.5	ns	1, 7, 8		

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Notes:

1. Minimum limits are guaranteed on Propagation Delays.
- * See "Parameter Measurement Information" in the General Information Section.

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AC OPERATING REQUIREMENTS

Sym.	Parameter	'FCT543T				'FCT543AT				'FCT543CT				Units	Fig. No.*		
		MIL		COM'L		MIL		COM'L		MIL		COM'L					
		Min. ¹	Max.														
t_s (H) t_s (L)	Set-up Time HIGH or LOW A_n or B_n to LEBA or LEAB	3.0	—	3.0	—	2.0	—	2.0	—	2.0	—	2.0	—	ns	9		
t_h (H) t_h (L)	Hold Time HIGH or LOW A_n or B_n to LEBA or LEAB	2.0	—	2.0	—	2.0	—	2.0	—	2.0	—	2.0	—	ns	9		
t_w	LEBA or LEAB Pulse Width LOW	5.0	—	5.0	—	5.0	—	5.0	—	5.0	—	5.0	—	ns	6		

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Note:

- * See "Parameter Measurement Information" in the General Information Section.

ORDERING INFORMATION

CYxxFCT	xxxx	xx	X	
Temp. Class	Device type	Package	Processing	
			C	Commercial
			M	Military Temperature
			MB	MIL-STD-883, Class B
			P	Plastic DIP
			D	CERDIP
			SO	Small Outline IC
			L	Leadless Chip Carrier
			Q	QSOP
		543		Non-Inverting Octal Latched Transceiver
		543A		Fast Non-Inverting Octal Latched Transceiver
		543C		Ultrafast Non-Inverting Octal Latched Transceiver
			74	Commercial
			54	Military

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